[EQUATION 1]

NUMBER OF MEASURED POINTS WITHIN ALLOWABLE ANGLE BETWEEN LATTICE PLANE {101} AND FILM SURFACE

{101} ORIENTATION RATIO

TOTAL NUMBER OF MEASURED POINTS





## [TABLE 1]

ITEMS		FIRST AMORPHOUS SEMICONDUCTOR FILM	SECOND AMORPHOUS SEMICONDUCTOR FILM
SiH₄FLOW AMOUNT	[sccm]	50 <b>~</b> 95	100
GeH₄(H₂-BASE 10%) FLOW AMOUNT	[sccm]	50 <b>~</b> 5	0
RF POWER	[W/cm <sup>2</sup> ]	0.35	<del>-</del>
PULSE FREQUENCY	[KHz]	10	<b>←</b>
DUTY	[%]	30	<del>-</del>
PRESSURE	[Pa]	33.25	<b>—</b>
SUBSTRATE TEMPERATURE (Tsub)	[°C]	300	<del></del>
ELECTRODE GAP (GAP)	[mm]	35	<del></del>